IEEE EDS Kansai Chapter Awards 2012

■ IEEE EDS Kansai Chapter of the Year Award

Authors: **N. Nakanishi**
Title: "High Reliable Strain Measurement For Power Devices Using STEM-CBED Method"
Coauthors: H. Aie, H. Maeda, Y. Hirose, N. Hattori, T. Koyama and E. Murakami
Affiliation: Renesas Electronics Corp.

■ IEEE EDS Kansai Chapter MFSK Award

Authors: **Yusuke Yamashiro**
Title: "Electric-Field-induced band gap of bilayer graphene in ionic liquid"
Coauthors: Yasuhide Ohno, Kenzo Maehashi, Koichi Inoue and Kazuhiko Matsumoto
Affiliation: Osaka University

Authors: **Fumio Mochizuki[1]**
Title: "Mobility Improvement in Top-Gate Benzothienobenzothiophene Organic Transistors Processed by Spin Coating"
Coauthors: Toshiyuki Endo[1], Takashi Nagase[1,2], Takashi Kobayashi[1,2], Kazuo Takimiya[3], Masaaki Ikeda[4,5], Hiroyoshi Naito[1,2]
Affiliation: [1]Osaka Prefecture University, [2]RIMED, Osaka Prefecture University, [3]Hiroshima University, [4]Nippon Kayaku Co., Ltd., [5]Kyushu University

■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Authors: **Hiroki Niwa, Jun Suda and Tsunenobu Kimoto** Paper ID: C-1
Title: "Fundamental Study on Junction Termination Structures for Ultrahigh-Voltage SiC PiN Diodes"
Affiliation: Kyoto University

■ IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: **Takamasa Kurumi** Paper ID: PA-02
Title: "TEM observation of directly bonded interface between Si and SiC"
Coauthors: Ryosuke Araki, Hiroyuki Kinoshita and Masahiro Yoshimoto
Affiliation: Kyoto Institute of Technology

Author: **Gota Murai[1]** Paper ID: PA-03
Title: "Photoluminescence study on recrystallization of ultra-shallow junction towards in-line measurements"
Coauthors: Masashi Okutani[1], Hiroki Saikusa[1], Masahiro Yoshimoto[1],Woo Sik Yoo[2]
Affiliation: [1]Kyoto Institute of Technology, [2]WaferMasters, Inc.

Author: **Yasuaki Miyoshi[1]** Paper ID: PB-05
Title: "Numerical simulation of transport properties in InAs/Si heterojunction nanowire tunneling field effect transistors"
Coauthors: Matsuto Ogawa[1], Satofumi Souma[1], Hajime Nakamura[2]
Affiliation: [1]Kobe University, [2]IBM Japan

Author: **Masashi Inoue[1]** Paper ID: PC-01

Title: “Characteristic Shift of a CTFT Inverter using n-type IGZO and p-type F8T2 TFTs after Temperature and Operation Stresses”

Coauthors: Takayuki Hasegawa[1], Takashi Nakanishi[1], Mutsumi Kimura[1], Kenji Nomura[2], Toshio Kamiya[2], Hideo Hosono[2]

Affiliation: [1]Ryukoku University, [2]Tokyo Institute of Technology

Author: **Norimitsu Wakama[1]** Paper ID: PC-03

Title: “A polarization analyzing CMOS image sensor with metal wire grid in 65-nm standard CMOS technology”

Coauthors: Hitoshi Matsuoka[1], Keisuke Ando[1], Toshihiko Noda[1,2], Kiyotaka Sasagawa[1,2], Takashi Tokuda[1,2], Jun Ohta[1,2]

Affiliation: [1]Nara Institute of Science and Technology, [2]CREST